

CMOS ASYNCHRONOUS FIFO 256 x 9, 512 x 9 and 1,024 x 9

IDT7200L IDT7201LA IDT7202LA

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

FEATURES:

- · First-In/First-Out dual-port memory
- 256 x 9 organization (IDT7200)
- 512 x 9 organization (IDT7201)
- 1,024 x 9 organization (IDT7202)
- Low power consumption
 - Active: 440mW (max.)
 - -Power-down: 28mW (max.)
- Ultra high speed—12ns access time
- Asynchronous and simultaneous read and write
- · Fully expandable by both word depth and/or bit width
- 720x family is pin and functionally compatible from 256 x 9 to 64k x 9
- Status Flags: Empty, Half-Full, Full
- Auto-retransmit capability
- High-performance CEMOS™ technology
- Military product compliant to MIL-STD-883, Class B
- Standard Military Drawing #5962-87531, 5962-89666, 5962-89863 and 5962-89536 are listed on this function
- Dual versions available in the TSSOP package. For more information, see IDT7280/7281/7282 data sheet

 $IDT7280 = 2 \times IDT7200$

 $IDT7281 = 2 \times IDT7201$

 $IDT7282 = 2 \times IDT7202$

- Industrial temperature range (-40°C to +85°C) is available (plastic packages only)
- Green parts available, see ordering information

DESCRIPTION:

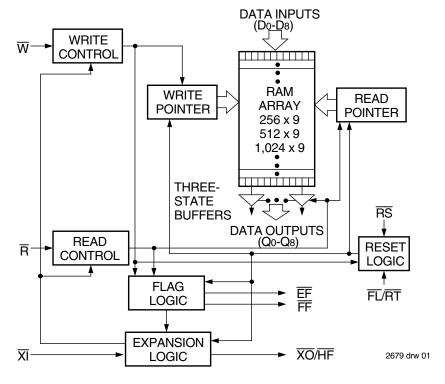
The IDT7200/7201/7202 are dual-port memories that load and empty data on a first-in/first-out basis. The devices use Full and Empty flags to prevent data overflow and underflow and expansion logic to allow for unlimited expansion capability in both word size and depth.

The reads and writes are internally sequential through the use of ring pointers, with no address information required to load and unload data. Data is toggled in and out of the devices through the use of the Write (\overline{W}) and Read (\overline{R}) pins.

The devices utilize a 9-bit wide data array to allow for control and parity bits at the user's option. This feature is especially useful in data communications applications where it is necessary to use a parity bit for transmission/reception error checking. It also features a Retransmit (\overline{RT}) capability that allows for reset of the read pointer to its initial position when \overline{RT} is pulsed LOW to allow for retransmission from the beginning of data. A Half-Full Flag is available in the single device mode and width expansion modes.

These FIFOs are fabricated using high-speed CMOS technology. They are designed for those applications requiring asynchronous and simultaneous read/writes in multiprocessing and rate buffer applications. Military grade product is manufactured in compliance with MIL-STD-883, Class B.

FUNCTIONAL BLOCK DIAGRAM



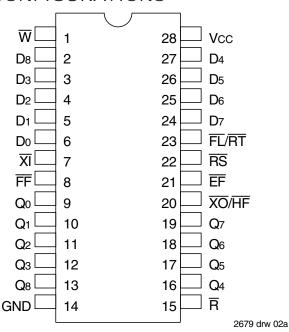
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COMMERCIAL, INDUSTRIAL AND MILITARY TEMPERATURE RANGES

NOVEMBER 2017

DSC-2679/15

PIN CONFIGURATIONS



	Reference	Order
Package Type	Identifier	Code
PLASTIC DIP(1)	P28-1	P
PLASTIC THIN DIP	P28-2	TP
CERDIP ⁽¹⁾	D28-1	D
THIN CERDIP	D28-3	TD
SOIC	SO28-3	SO.

TOP VIEW

INDEX 1 32 31 30 4 3 2 29 D₆ D_2 D₁ 6 28 D₇ D₀ 27 NC \overline{XI} 26 FL/RT FF $\overline{\mathsf{RS}}$ 9 25 **EF** Q_0 10 24 23 XO/HF Q1 11 12 NC 22 Q7 Q2 13 21 Q₆ 14 15 16 17 18 19 20 S S S N 2679 drw 02b

Package Type	Reference Identifier	Order Code
LCC ⁽¹⁾	L32- 1	L
PLCC	J32-1	J

TOP VIEW

NOTE:

1. The 600-mil-wide DIP (P28-1 and D28-1) and LCC are not available for the IDT7200.

ABSOLUTE MAXIMUM RATINGS

Symbol	Rating	Com'l & Ind'l	Mil.	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
Tstg	Storage Temperature	-55 to +125	-65 to +155	°C
Іоит	DC Output Current	-50 to +50	-50 to +50	mA

NOTE:

Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause
permanent damage to the device. This is a stress rating only and functional operation of
the device at these or any other conditions above those indicated in the operational
sections of this specification is not implied. Exposure to absolute maximum rating
conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
	Commercial/Industrial/Military				
GND	Supply Voltage	0	0	0	٧
VIH ⁽¹⁾	Input High Voltage Com'l/Ind'l	2.0	_	_	V
VIH ⁽¹⁾	Input High Voltage Military	2.2	_	_	٧
VIL ⁽²⁾	Input Low Voltage		_	0.8	V
	Commercial/Industrial/Military				
TA	Operating Temperature Commercial	0	_	70	°C
TA	Operating Temperature Industrial	-40		85	°C
TA	Operating Temperature Military	-55	_	125	°C

- 1. For $\overline{RT}/\overline{RS}/\overline{XI}$ input, Vih = 2.6V (commercial). For $\overline{RT}/\overline{RS}/\overline{XI}$ input, Vih = 2.8V (military).
- 2. 1.5V undershoots are allowed for 10ns once per cycle.

DC ELECTRICAL CHARACTERISTICS

(Commercial: $Vcc = 5V \pm 10\%$, $TA = 0^{\circ}C$ to $+70^{\circ}C$; Industrial: $Vcc = 5V \pm 10\%$, $TA = -40^{\circ}C$ to $+85^{\circ}C$; Military: $Vcc = 5V \pm 10\%$, $TA = -55^{\circ}C$ to $+125^{\circ}C$)

		IDT7200L IDT7201LA IDT7202LA Com'l & Ind'I ⁽¹⁾ ta = 12, 15, 20, 25, 35, 50 ns		IDT7200L IDT7201LA IDT7202LA Military ⁽²⁾ tA = 20, 30, 50, 80 ns		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
ILI ⁽³⁾	Input Leakage Current (Any Input)	- 1	1	-10	10	μΑ
ILO ⁽⁴⁾	Output Leakage Current	-10	10	-10	10	μΑ
Vон	Output Logic "1" Voltage Iон = -2mA	2.4	_	2.4		V
Vol	Output Logic "0" Voltage IoL = 8mA	_	0.4	_	0.4	V
ICC1 ^(5,6,7)	Active Power Supply Current	_	80	_	100	mA
ICC2 ^(5,8)	Standby Current ($\overline{R}=\overline{W}=\overline{RS}=\overline{FL}/\overline{RT}=VIH$)	_	5	_	15	mA

NOTES:

- 1. Industrial temperature range product for the 15ns and 25 ns speed grades are available as a standard device.
- 2. Military speed grades of 50ns and 80ns are only available for the IDT7201LA.
- 3. Measurements with $0.4 \le VIN \le VCC$.
- 4. $\overline{R} \ge V_{IH}$, $0.4 \le V_{OUT} \le V_{CC}$.
- 5. Tested with outputs open (Iout = 0).
- 6. Tested at f = 20 MHz.
- 7. Typical lcc1 = 15 + 2*fs + 0.02*CL*fs (in mA) with Vcc = 5V, TA = 25°C, fs = WCLK frequency = RCLK frequency (in MHz, using TTL levels), data switching at fs/2, CL = capacitive load (in pF).
- 8. All Inputs = Vcc 0.2V or GND + 0.2V.

CAPACITANCE (TA = +25°C, f = 1.0 MHz)

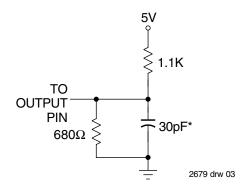
Symbol	Parameter	Condition	Max.	Unit
CIN	Input Capacitance	VIN = 0V	8	pF
Соит	Output Capacitance	Vout = 0V	8	pF

NOTE:

1. Characterized values, not currently tested.

AC TEST CONDITIONS

NO LEST CONDITIONS					
Input Pulse Levels	GND to 3.0V				
Input Rise/Fall Times	5ns				
Input Timing Reference Levels	1.5V				
Output Reference Levels	1.5V				
Output Load	See Figure 1				



or equivalent circuit

* Figure 1. Output Load

* Includes scope and jig capacitances.

AC ELECTRICAL CHARACTERISTICS(1)

(Commercial: $Vcc = 5V \pm 10\%$, $TA = 0^{\circ}C$ to $+70^{\circ}C$; Industrial: $Vcc = 5V \pm 10\%$, $TA = -40^{\circ}C$ to $+85^{\circ}C$; Military: $Vcc = 5V \pm 10\%$, $TA = -55^{\circ}C$ to $+125^{\circ}C$)

		Commercial		Com'l & Ind'l ⁽²⁾		Com'l & Mil.		Com'l	& Ind'l ⁽²⁾	
			200L12 01LA12 02LA12	12 IDT7201LA15		IDT720	00L20 01LA20 02LA20	IDT720	200L25 01LA25 02LA25	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
ts	ShiftFrequency	_	50	_	40	_	33.3	_	28.5	MHz
trc	Read Cycle Time	20	_	25	_	30	_	35	_	ns
tA	Access Time	-	12	_	15	_	20	_	25	ns
trr	Read Recovery Time	8	_	10	_	10	_	10	_	ns
trpw	Read Pulse Width ⁽³⁾	12	_	15	_	20	_	25	_	ns
trlz	Read Pulse Low to Data Bus at Low Z ⁽⁴⁾	3	_	3	_	3	_	3	_	ns
twLz	Write Pulse High to Data Bus at Low Z ^(4,5)	5	_	5	_	5	_	5	_	ns
tov	Data Valid from Read Pulse High	5	_	5	_	5	_	5	_	ns
trhz	Read Pulse High to Data Bus at High Z ⁽⁴⁾	<u> </u>	12	_	15	_	15	_	18	ns
twc	Write Cycle Time	20	_	25	_	30		35		ns
twpw	Write Pulse Width ⁽³⁾	12	_	15	_	20	_	25	_	ns
twr	Write Recovery Time	8	_	10	_	10	_	10	_	ns
tos	Data Set-up Time	9	_	11	_	12	_	15	_	ns
tDH .	Data Hold Time	0	_	0	_	0	_	0	_	ns
trsc	Reset Cycle Time	20	_	25	_	30	_	35	_	ns
trs	Reset Pulse Width ⁽³⁾	12	_	15	_	20	_	25	_	ns
trss	Reset Set-up Time ⁽⁴⁾	12	_	15	_	20	_	25	_	ns
trsr	Reset Recovery Time	8	_	10	_	10	_	10	_	ns
trtc	Retransmit Cycle Time	20	_	25	_	30	_	35		ns
trt	Retransmit Pulse Width ⁽³⁾	12	_	15	_	20	_	25	_	ns
trts	Retransmit Set-up Time ⁽⁴⁾	12	_	15	_	20	_	25	_	ns
trtr	Retransmit Recovery Time	8	_	10	_	10	_	10	_	ns
tefl	Reset to Empty Flag Low	<u> </u>	12	_	25	_	30	_	35	ns
thfh,ffh	Reset to Half-Full and Full Flag High	<u> </u>	17	_	25	_	30	_	35	ns
trtf	Retransmit Low to Flags Valid	T -	20	_	25	_	30	_	35	ns
tref	Read Low to Empty Flag Low	<u> </u>	12	_	15	_	20	_	25	ns
trff	Read High to Full Flag High	<u> </u>	14	_	15	_	20	_	25	ns
trpe	Read Pulse Width after EF High	12	_	15	_	20	_	25		ns
twer	Write High to Empty Flag High	T -	12	_	15	_	20	_	25	ns
twff	Write Low to Full Flag Low	 	14	_	15	<u> </u>	20	_	25	ns
twhF	Write Low to Half-Full Flag Low	 _	17	_	25	_	30	_	35	ns
trhf	Read High to Half-Full Flag High	 _	17	_	25	_	30	_	35	ns
twpf	Write Pulse Width after FF High	12	_	15	_	20	_	25	_	ns
txol	Read/Write to XO Low	<u> </u>	12	_	15	_	20	_	25	ns
tхон	Read/Write to XO High	<u> </u>	12	_	15	_	20	_	25	ns
txı	XI Pulse Width ⁽³⁾	12	_	15	_	20	_	25	_	ns
txir	XI Recovery Time	8	_	10	_	10	_	10	_	ns
txis	XI Set-up Time	8	_	10	_	10	_	10	_	ns

- 1. Timings referenced as in AC Test Conditions.
- 2. Industrial temperature range product for 15ns and 25ns speed grades are available as a standard device.
- 3. Pulse widths less than minimum value are not allowed.
- 4. Values guaranteed by design, not currently tested.
- 5. Only applies to read data flow-through mode

AC ELECTRICAL CHARACTERISTICS(1) (Continued)

(Commercial: $VCC = 5V \pm 10\%$, $TA = 0^{\circ}C$ to $+70^{\circ}C$; Industrial: $VCC = 5V \pm 10\%$, $TA = -40^{\circ}C$ to $+85^{\circ}C$; Military: $VCC = 5V \pm 10\%$, $TA = -55^{\circ}C$ to $+125^{\circ}C$)

			itary	Commercial		Com'l	& Mil. ⁽²⁾	Milita	ary ⁽²⁾	Т
		IDT72	200L30 01LA30 02LA30	IDT7200L35 IDT7200L50 IDT7201LA50 IDT7202LA55 IDT7202LA50 IDT7202LA50		IDT720	1LA80			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
ts	ShiftFrequency		25		22.2	_	15	_	10	MHz
trc	Read Cycle Time	40		45	_	65	_	100		ns
tA	Access Time		30		35		50		80	ns
trr	Read Recovery Time	10	_	10	_	15		20		ns
trpw	Read Pulse Width ⁽³⁾	30	_	35	_	50	_	80	_	ns
trlz	Read Pulse Low to Data Bus at Low Z ⁽⁴⁾	3	_	3	_	3	_	3	_	ns
twLz	Write Pulse High to Data Bus at Low Z ^(4,5)	5	_	5	_	5	_	5	_	ns
tov	Data Valid from Read Pulse High	5	_	5	_	5	_	5	_	ns
trhz	Read Pulse High to Data Bus at High Z ⁽⁴⁾	_	20	_	20	_	30	_	30	ns
twc	Write Cycle Time	40	_	45	_	65	_	100	_	ns
twpw	Write Pulse Width ⁽³⁾	30	_	35	_	50	_	80	_	ns
twr	Write Recovery Time	10	_	10	_	15	_	20	_	ns
tos	Data Set-up Time	18	_	18	_	30	_	40	_	ns
tDH .	Data Hold Time	0	_	0	_	5	_	10	_	ns
trsc	Reset Cycle Time	40	_	45	_	65	_	100	_	ns
trs	Reset Pulse Width ⁽³⁾	30	_	35	_	50	_	80	_	ns
trss	Reset Set-up Time ⁽⁴⁾	30	_	35	_	50	_	80	_	ns
trsr	Reset Recovery Time	10	_	10	_	15	_	20	_	ns
trtc	Retransmit Cycle Time	40	_	45	_	65	_	100	_	ns
trt	Retransmit Pulse Width ⁽³⁾	30	_	35	_	50	_	80	_	ns
trts	Retransmit Set-up Time ⁽⁴⁾	30	_	35	_	50	_	80	_	ns
trtr	Retransmit Recovery Time	10	_	10	_	15	_	20	_	ns
tefl	Reset to Empty Flag Low	_	40	_	45	_	65	_	100	ns
theh,eeh	Reset to Half-Full and Full Flag High	_	40	_	45	_	65	_	100	ns
trtf	Retransmit Low to Flags Valid	_	40	_	45	_	65	_	100	ns
tref	Read Low to Empty Flag Low		30	_	30	_	45	_	60	ns
trff	Read High to Full Flag High	_	30	_	30	_	45	_	60	ns
trpe	Read Pulse Width after EF High	30	_	35	_	50	_	80	_	ns
twer	Write High to Empty Flag High	_	30	_	30	_	45	_	60	ns
twff	Write Low to Full Flag Low	_	30	_	30	_	45	_	60	ns
twhF	Write Low to Half-Full Flag Low	_	40	_	45	_	65	_	100	ns
trhf	Read High to Half-Full Flag High	_	40	_	45	_	65	_	100	ns
twpf	Write Pulse Width after FF High	30	_	35	_	50	_	80	_	ns
txol	Read/Write to XO Low		30	_	35	_	50	_	80	ns
tхон	Read/Write to XO High		30	_	35	_	50	_	80	ns
txı	XI Pulse Width ⁽³⁾	30	_	35	_	50		80		ns
txir	XI Recovery Time	10	_	10	_	10	_	10		ns
txis	XI Set-up Time	10	_	10	_	15	_	15	_	ns

- 1. Timings referenced as in AC Test Conditions
- 2. Military speed grades of 50ns and 80ns are only available for IDT7201LA.
- 3. Pulse widths less than minimum value are not allowed.
- 4. Values guaranteed by design, not currently tested.
- 5. Only applies to read data flow-through mode.

SIGNAL DESCRIPTIONS

INPUTS:

DATA IN (Do - D8)

Data inputs for 9-bit wide data.

CONTROLS:

RESET (RS)

Reset is accomplished whenever the Reset (\overline{RS}) input is taken to a LOW state. During reset, both internal read and write pointers are set to the first location. A reset is required after power up before a write operation can take place. Both the Read Enable (\overline{R}) and Write Enable (\overline{W}) inputs must be in the HIGH state during the window shown in Figure 2, (i.e., trss before the rising edge of \overline{RS}) and should not change until trsr after the rising edge of \overline{RS} . Half-Full Flag (\overline{HF}) will be reset to HIGH after Reset (\overline{RS}).

WRITE ENABLE (W)

A write cycle is initiated on the falling edge of this input if the Full Flag (\overline{FF}) is not set. Data set-up and hold times must be adhered to with respect to the rising edge of the Write Enable (\overline{W}) . Data is stored in the RAM array sequentially and independently of any on-going read operation.

After half of the memory is filled and at the falling edge of the next write operation, the Half-Full Flag ($\overline{\text{HF}}$) will be set to LOW and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag ($\overline{\text{HF}}$) is then reset by the rising edge of the read operation.

To prevent data overflow, the Full Flag (\overline{FF}) will go LOW, inhibiting further write operations. Upon the completion of a valid read operation, the Full Flag (\overline{FF}) will go HIGH after tRFF, allowing a valid write to begin. When the FIFO is full, the internal write pointer is blocked from \overline{W} , so external changes in \overline{W} will not affect the FIFO when it is full.

READ ENABLE (R)

Aread cycle is initiated on the falling edge of the Read Enable (\overline{R}) provided the Empty Flag (\overline{EF}) is not set. The data is accessed on a First-In/First-Out basis, independent of any ongoing write operations. After Read Enable (\overline{R}) goes HIGH, the Data Outputs (Q0-Q8) will return to a high impedance condition until the next Read operation. When all data has been read from the FIFO, the Empty Flag (\overline{EF}) will go LOW, allowing the "final" read cycle but inhibiting further read operations with the data outputs remaining in a high impedance state. Once a valid write operation has been accomplished, the Empty Flag (\overline{EF}) will go HIGH after twef and a valid Read can then begin. When the FIFO is empty, the internal read pointer is blocked from \overline{R} so external changes in \overline{R} will not affect the FIFO when it is empty.

FIRST LOAD/RETRANSMIT (FL/RT)

This is a dual-purpose input. In the Depth Expansion Mode, this pin is grounded to indicate that it is the first loaded (see Operating Modes). In the Single

Device Mode, this pin acts as the retransmit input. The Single Device Mode is initiated by grounding the Expansion In (\overline{XI}) .

The IDT7200/7201A/7202A can be made to retransmit data when the Retransmit Enable control (\overline{RT}) input is pulsed LOW. A retransmit operation will set the internal read pointer to the first location and will not affect the write pointer. Read Enable (\overline{R}) and Write Enable (\overline{W}) must be in the HIGH state during retransmit. This feature is useful when less than 256/512/1,024 writes are performed between resets. The retransmit feature is not compatible with the Depth Expansion Mode and will affect the Half-Full Flag (\overline{HF}), depending on the relative locations of the read and write pointers.

EXPANSION IN (XI)

This input is a dual-purpose pin. Expansion In (\overline{XI}) is grounded to indicate an operation in the single device mode. Expansion In (\overline{XI}) is connected to Expansion Out (\overline{XO}) of the previous device in the Depth Expansion or Daisy Chain Mode.

OUTPUTS:

FULL FLAG (FF)

The Full Flag ($\overline{\text{FF}}$) will go LOW, inhibiting further write operation, when the write pointer is one location less than the read pointer, indicating that the device is full. If the read pointer is not moved after Reset ($\overline{\text{RS}}$), the Full-Flag ($\overline{\text{FF}}$) will go LOW after 256 writes for IDT7200, 512 writes for the IDT7201A and 1.024 writes for the IDT7202A.

EMPTY FLAG (EF)

The Empty Flag $(\overline{\text{EF}})$ will go LOW, inhibiting further read operations, when the read pointer is equal to the write pointer, indicating that the device is empty.

EXPANSION OUT/HALF-FULL FLAG (XO/HF)

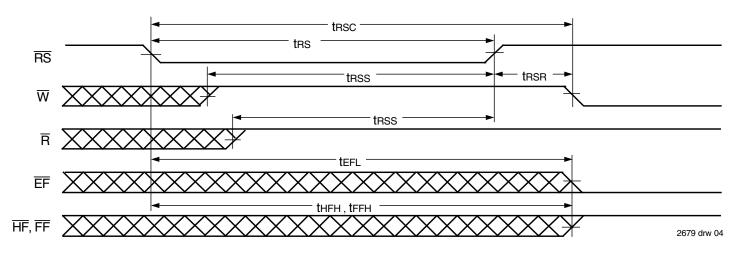
This is a dual-purpose output. In the single device mode, when Expansion In (\overline{XI}) is grounded, this output acts as an indication of a half-full memory.

After half of the memory is filled and at the falling edge of the next write operation, the Half-Full Flag ($\overline{\text{HF}}$) will be set LOW and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag ($\overline{\text{HF}}$) is then reset by using rising edge of the read operation.

In the Depth Expansion Mode, Expansion In (\overline{XI}) is connected to Expansion Out (\overline{XO}) of the previous device. This output acts as a signal to the next device in the Daisy Chain by providing a pulse to the next device when the previous device reaches the last location of memory.

DATA OUTPUTS (Q0 - Q8)

Data outputs for 9-bit wide data. This data is in a high impedance condition whenever Read (\overline{R}) is in a HIGH state.



- 1. EF, FF, HF may change status during Reset, but flags will be valid at trsc.
- 2. \overline{W} and $\overline{R} = V_{IH}$ around the rising edge of \overline{RS} .

Figure 2. Reset

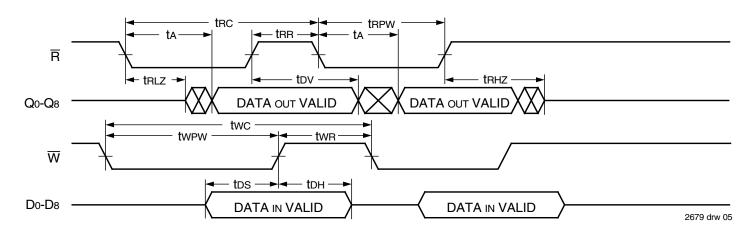


Figure 3. Asynchronous Write and Read Operation

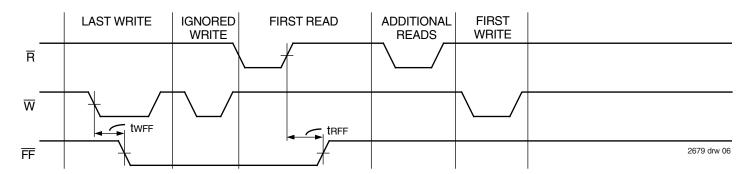


Figure 4. Full Flag From Last Write to First Read

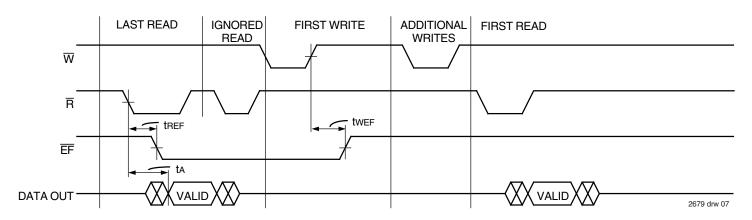


Figure 5. Empty Flag From Last Read to First Write

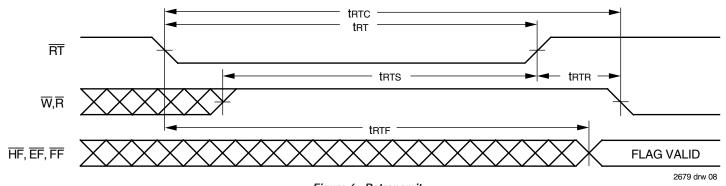


Figure 6. Retransmit

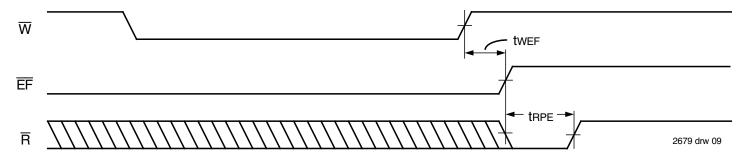


Figure 7. Minimum Timing for an Empty Flag Coincident Read Pulse

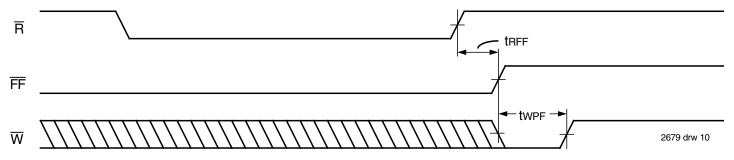


Figure 8. Minimum Timing for a Full Flag Coincident Write Pulse

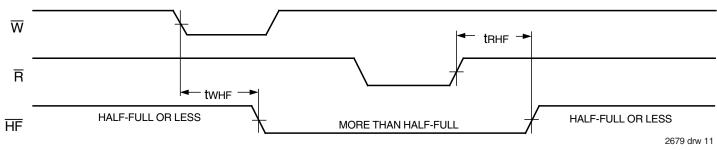


Figure 9. Half-Full Flag Timing

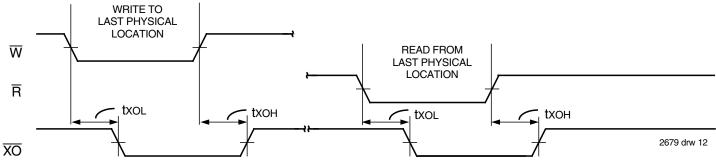


Figure 10. Expansion Out

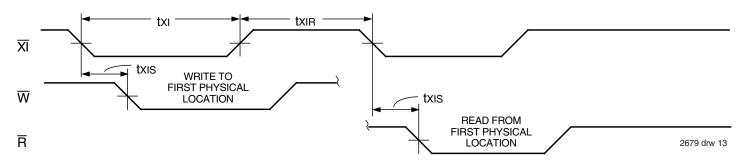


Figure 11. Expansion In

OPERATING MODES:

Care must be taken to assure that the appropriate flag is monitored by each system (i.e. \overline{FF} is monitored on the device where \overline{W} is used; \overline{EF} is monitored on the device where \overline{R} is used). For additional information, refer to Tech Note 8: Operating FIFOs on Full and Empty Boundary Conditions and Tech Note 6: Designing with FIFOs.

SINGLE DEVICE MODE

A single IDT7200/7201A/7202A may be used when the application requirements are for 256/512/1,024 words or less. These devices are in a Single Device Configuration when the Expansion In (\overline{XI}) control input is grounded (see Figure 12).

DEPTH EXPANSION

The IDT7200/7201A/7202A can easily be adapted to applications when the requirements are for greater than 256/512/1,024 words. Figure 14 demonstrates Depth Expansion using three IDT7200/7201A/7202As. Any

depth can be attained by adding additional IDT7200/7201A/7202As. These FIFOs operate in the Depth Expansion mode when the following conditions are met:

- 1. The first device must be designated by grounding the First Load (FL) control input.
- 2. All other devices must have FL in the HIGH state.
- 3. The Expansion Out (\overline{XO}) pin of each device must be tied to the Expansion In (\overline{XI}) pin of the next device. See Figure 14.
- 4. External logic is needed to generate a composite Full Flag (FF) and Empty Flag (EF). This requires the ORing of all EFs and ORing of all FFs (i.e. all must be set to generate the correct composite FF or EF). See Figure 14.
- 5. The Retransmit (RT) function and Half-Full Flag (HF) are not available in the Depth Expansion Mode.

For additional information, refer to Tech Note 9: Cascading FIFOs or FIFO Modules.

USAGE MODES:

WIDTH EXPANSION

Word width may be increased simply by connecting the corresponding input control signals of multiple devices. Status flags (EF, FF and HF) can be detected from any one device. Figure 13 demonstrates an 18-bit word width by using two IDT7200/7201A/7202As. Any word width can be attained by adding additional IDT7200/7201A/7202As (Figure 13).

BIDIRECTIONAL OPERATION

Applications which require data buffering between two systems (each system capable of Read and Write operations) can be achieved by pairing IDT7200/7201A/7202As as shown in Figure 16. Both Depth Expansion and Width Expansion may be used in this mode.

DATA FLOW-THROUGH

Two types of flow-through modes are permitted, a read flow-through and write flow-through mode. For the read flow-through mode (Figure 17),

the FIFO permits a reading of a single word after writing one word of data into an empty FIFO. The data is enabled on the bus in (twef+ta) ns after the rising edge of \overline{W} , called the first write edge, and it remains on the bus until the \overline{R} line is raised from LOW-to-HIGH, after which the bus would go into a three-state mode after trazens. The \overline{EF} line would have a pulse showing temporary deassertion and then would be asserted.

In the write flow-through mode (Figure 18), the FIFO permits the writing of a single word of data immediately after reading one word of data from a full FIFO. The $\overline{\mathbb{R}}$ line causes the $\overline{\mathbb{FF}}$ to be deasserted but the $\overline{\mathbb{W}}$ line being LOW causes it to be asserted again in anticipation of a new data word. On the rising edge of $\overline{\mathbb{W}}$, the new word is loaded in the FIFO. The $\overline{\mathbb{W}}$ line must be toggled when $\overline{\mathbb{FF}}$ is not asserted to write new data in the FIFO and to increment the write pointer.

COMPOUND EXPANSION

The two expansion techniques described above can be applied together in a straightforward manner to achieve large FIFO arrays (see Figure 15).

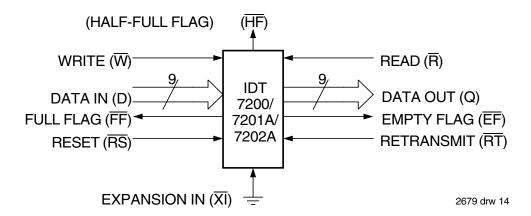


Figure 12. Block Diagram of Single 256 x 9, 512 x 9, 1,024 x 9 FIFO

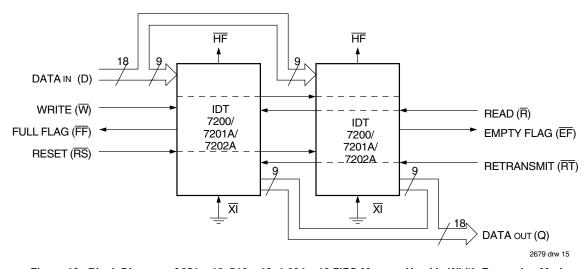


Figure 13. Block Diagram of 256 x 18, 512 x 18, 1,024 x 18 FIFO Memory Used in Width Expansion Mode

TABLE 1 — RESET AND RETRANSMIT

Single Device Configuration/Width Expansion Mode

		Inputs		Interna	Outputs			
Mode	RS	RT	Χī	Read Pointer	Write Pointer	ĒĒ	FF	HF
Reset	0	Χ	0	Location Zero	LocationZero	0	1	1
Retransmit	1	0	0	Location Zero	Unchanged	Χ	Χ	Χ
Read/Write	1	1	0	Increment ⁽¹⁾	Increment ⁽¹⁾	Х	Χ	Χ

NOTE:

TABLE 2 — RESET AND FIRST LOAD TRUTH TABLE

Depth Expansion/Compound Expansion Mode

		Inputs		Interna	I Status	Outputs		
Mode	RS	FL	Χī	Read Pointer	Write Pointer	ĒĒ	FF	
Reset First Device	0	0	(1)	Location Zero	LocationZero	0	1	
Reset All Other Devices	0	1	(1)	Location Zero	Location Zero	0	1	
Read/Write	1	Х	(1)	Χ	Χ	Х	Х	

NOTF.

1. \overline{XI} is connected to \overline{XO} of previous device. See Figure 14. \overline{RS} = Reset Input, $\overline{FL/RT}$ = First Load/Retransmit, \overline{EF} = Empty Flag Output, \overline{FF} = Full Flag Output, \overline{XI} = Expansion Input, \overline{HF} = Half-Full Flag Output

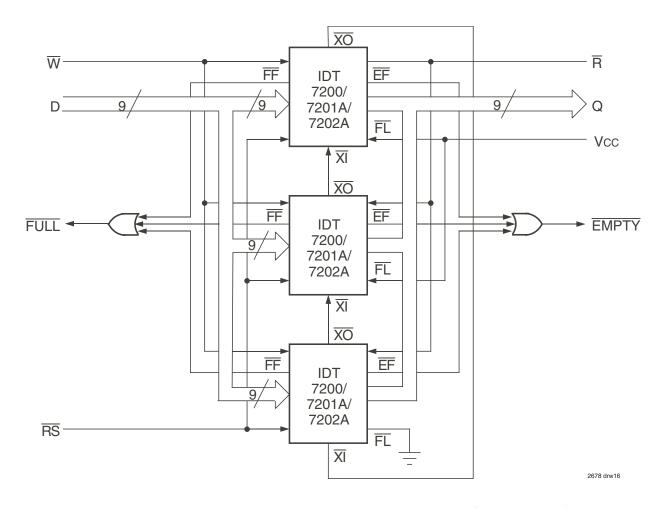
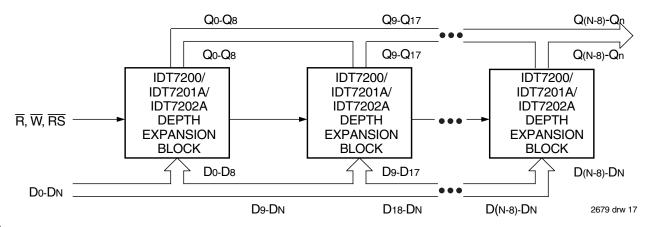


Figure 14. Block Diagram of 768 x 9, 1,536 x 9, 3,072 x 9 FIFO Memory (Depth Expansion)

^{1.} Pointer will increment if flag is HIGH.



- 1. For depth expansion block see section on Depth Expansion and Figure 14.
- 2. For Flag detection see section on Width Expansion and Figure 13.

Figure 15. Compound FIFO Expansion

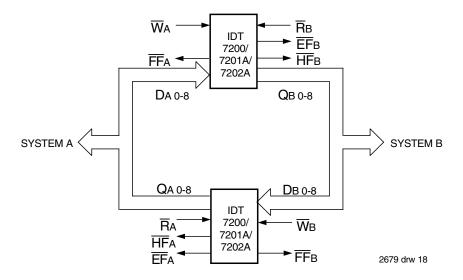


Figure 16. Bidirectional FIFO Mode

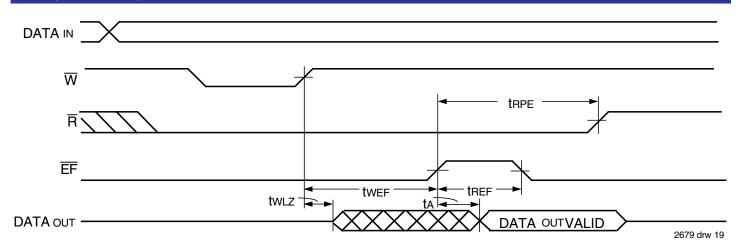


Figure 17. Read Data Flow-Through Mode

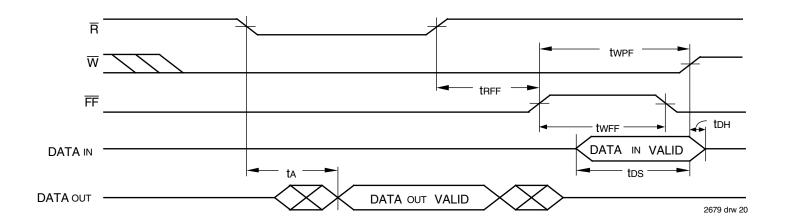
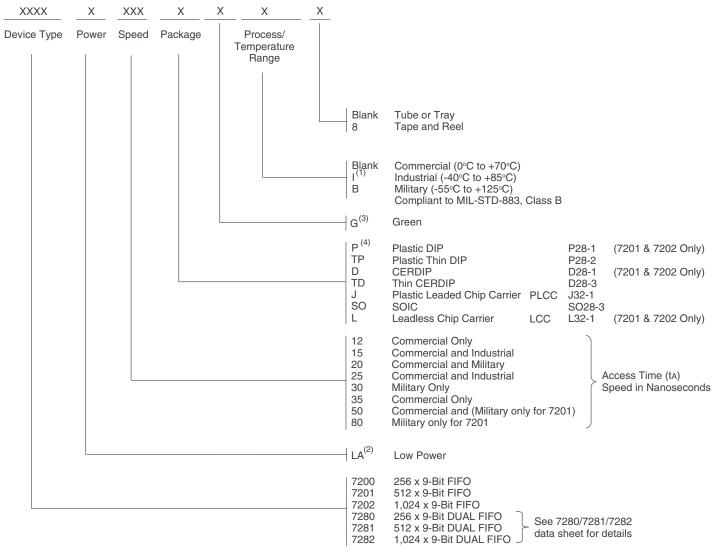


Figure 18. Write Data Flow-Through Mode

ORDERING INFORMATION



NOTES:

2679 drw 21

- 1. Industrial temperature range product is available for the 15ns and 25ns as a standard product.
- 2. "A" to be included for IDT7201 and IDT7202 ordering part number.
- Green parts are available. For specific speeds and packages contact your local sales office.
 LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice PDN# SP-17-02
- 4. For "P", Plastic Dip, when ordering green package, the suffix is "PDG".

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